

# PROGRAM TIME TABLE

Wednesday, September 22											
10:00-12:00 Opening & Plenary Sessions (Yasuda Auditorium)											
1F 211	1F 212	1F 213	2F 221	4F 241	4F 242	4F 243	4F 244	4F 245	4F 246	2F 222	2F 223
13:00-14:15 Area 10: A-1: Organic Device Physics	13:00-14:10 Area 1: B-1: Ge MOS Technology 1	13:00-14:20 Area 3: C-1: Low Frequency Noise	13:00-14:15 Area 7: D-1: Nonlinear Optics	13:00-14:20 Area 4: E-1: DRAM	13:00-14:15 Area 9: F-1: Graphene Structures and Transport	13:00-14:10 Area 5: G-1: RF Circuits and Systems (1)	13:00-14:15 Area 8: H-1: New Functional Materials	13:00-14:15 Area 6: I-1: III-V High-Speed and High-Frequency Transistors	13:00-14:15 Area 13: J-1: Carbon Nanotube Devices	13:30-14:00 Area 14: K-1: Modeling of Power LDMOSFET	13:00-14:15 Area 11: L-1: Biosensors
14:45-15:45 Area 10: A-2: Electric Characterization of Organic Semiconductors	14:45-16:05 Area 1: B-2: Ge MOS Technology 2	14:45-16:05 Area 3: C-2: Transport Physics	14:45-15:45 Area 7: D-2: Advanced Design and Measurement	14:45-16:05 Area 4: E-2: Flash Memory I	14:45-16:00 Area 9: F-2: Novel Structures	14:45-16:05 Area 5: G-2: RF Circuits and Systems (2)	14:45-16:00 Area 8: H-2: Growth of Grapheme for Electronics Applications	14:45-16:00 Area 6: I-2: GaN HEMTs	14:45-16:00 Area 13: J-2: Carbon Nanotube Properties and Transport	14:45-15:45 Area 14: K-2: Power Module Technology	14:45-16:00 Area 11: L-2: Silicon Based Biomedical Devices
17:00-18:30 Special Plenary Session (Tokyo Dome Hotel)											
18:30-20:00 Reception (Tokyo Dome Hotel)											
Thursday, September 23											
1F 211	1F 212	1F 213	2F 221	4F 241	4F 242	4F 243	4F 244	4F 245	4F 246	2F 222	2F 223
9:00-10:30 Area 10: A-3: Organic Light Emitting Diodes	9:00-10:30 Area 1: B-3: High-k Gate Stack	9:00-10:30 Area 3: C-3: Tunnel & Schottky-S/D FETs	9:00-10:45 Area 7: D-3: GaN LED	9:00-10:50 Area 4: E-3: Flash Memory II	9:00-10:45 Area 9: F-3: Spin Manipulation and Photon Detection	9:00-10:50 Area 5: G-3: Modeling, Variation and Reliability	9:00-10:30 Area 8: H-3: Oxides and Nanowires	9:00-10:30 Area 6: I-3: III-V Device Technologies	9:00-10:30 Area 13: J-3: Graphene Photonics and Electronics	9:00-10:30 Area 14: K-3: Compound Power Semiconductor Devices	9:00-10:30 Area 11: L-3: Nano Structures and Devices
11:00-12:15 Short Presentation Area 10	11:00-12:15 Short Presentation Area 1	11:00-12:15 Short Presentation Area 3	11:00-12:15 Short Presentation Area 7	11:00-12:15 Short Presentation Area 4	11:00-12:15 Short Presentation Area 9 and Area 12	11:00-12:15 Short Presentation Area 5	11:00-12:15 Short Presentation Area 2 and Area 8	11:00-12:15 Short Presentation Area 6	11:00-12:15 Short Presentation Area 13	11:00-12:15 Short Presentation Area 14	11:00-12:15 Short Presentation Area 11
13:15-14:45 Poster Session (Takeda Bldg.)											
1F 211	1F 212	1F 213	2F 221	4F 241	4F 242	4F 243	4F 244	4F 245	4F 246	2F 222	2F 223
15:10-16:25 Area 10: A-4: Organic Memory and Related Materials	15:10-16:20 Area 1: B-4: Process Integration	15:10-16:25 Area 3: C-4: Tr & SRAM Variabilities	15:10-16:25 Area 7: D-4: Photonic Crystal Devices	15:10-16:10 Area 4: E-4: Flash Memory III	15:10-16:25 Area 9: F-4: Quantum Dots	15:10-16:25 Area 5: G-4: Advanced Analog Circuits	15:10-16:20 Area 8: H-4: Carbon Interconnect	15:10-16:25 Area 6: I-4: Silicon Carbide Devices	15:10-16:25 Area 13: J-4: Graphene's Electrical Properties	15:10-16:25 Area 14: K-4: Next Generation Solar Cells	15:10-16:25 Area 11: L-4: Nano Structures and Devices
16:50-18:05 Area 10: A-5: Organic Electronics and Device Physics	16:50-18:10 Area 1: B-5: Advanced Gate Dielectrics	16:50-18:10 Area 3: C-5: Si Nanowire Technology	16:50-18:05 Area 7: D-5: Quantum Dot	16:50-17:30 Area 4: E-5: Flash Memory IV	16:50-18:05 Area 9: F-5: New Functional MOS Structures	16:50-18:05 Area 5: G-5: Integrated MEMS/Bio Sensors	16:50-18:00 Area 8: H-5: Cu/Low-k Integration	16:50-17:50 Area 6: I-5: Oxide Devices	16:50-18:05 Area 13: J-5: Graphene Devices	16:50-18:05 Area 14: K-5: Compound Semiconductor Solar Cells	16:50-18:05 Area 11: L-5: Nano Structures and Devices
18:30-20:00 Rump Session (Sanjyo Conference Hall)											
Friday, September 24											
1F 211	1F 212	1F 213	2F 221	2F 241	2F 242	4F 243	4F 244	4F 245	4F 246	2F 222	2F 223
9:00-10:45 Area 10: A-6: Organic Transistors and Device Physics I	9:00-10:45 Area 1: B-6: Junction Technology	9:00-10:45 Area 3: C-6: Advanced CMOS Technology	9:00-10:30 Area 7: D-6: Photonic and Electronic Integration	9:00-10:35 Area 4: E-6: FeRAM	9:30-10:45 Area 12: F-6: Spintronics (I) - Spin-related Phenomena and Applications -	9:00-10:45 Area 5&11: G-6: Image Sensors and Interface Circuits	9:10-10:50 Area 2: H-6: Cu Reliability	9:00-10:45 Area 6: I-6: GaN Power Transistors	9:00-10:45 Area 13: J-6: Nanowire Transistors	9:00-10:45 Area 8: K-6: Quantum Dots	
11:15-12:15 Area 10: A-7: Organic Transistors and Device Physics II	11:15-12:25 Area 1: B-7: Dopant Characterization	11:15-12:35 Area 3: C-7: FinFET Devices	11:15-12:00 Area 7: D-7: Nano Photonics	11:15-12:05 Area 4: E-7: MRAM	11:15-12:30 Area 12: F-7: Spintronics (II) - New Applications -	11:15-12:30 Area 5: G-7: Data Converter Circuits	11:15-12:25 Area 2: H-7: 3D Interconnect	11:15-12:30 Area 6: I-7: Processing and Interface Technologies	11:15-12:15 Area 13: J-7: Nanowire Growth and Applications	11:15-12:30 Area 8: K-7: Growth and Characterization of Nitrides	
13:30-15:00 Area 10: A-8: Organic Transistors and Device Fabrication I		13:30-15:10 Area 3: C-8: Gate-Insulator Reliability	13:30-15:15 Area 7: D-8: Si Photonics (1)	13:30-15:15 Area 4: E-8: PRAM/ReRAM	13:30-15:00 Area 12: F-8: Spintronics (III) - Semiconductors -	13:30-15:00 Area 11: G-8: Bio Nanofusion Technologies	13:30-14:55 Area 2: H-8: 3D Integration	13:30-15:15 Area 14: I-8: Crystalline and Thin Film Silicon Solar Cell ( I )		13:30-15:00 Area 8: K-8: Si and Ge-based Materials and Devices	
15:30-17:15 Area 10: A-9: Organic Transistors and Device Fabrication II	15:30-17:10 Area 1: B-9: Interface and Strain Characterization	15:30-17:15 Area 3: C-9: Emerging Device Technology	15:30-17:15 Area 7: D-9: Si Photonics (2)	15:30-17:15 Area 4: E-9: ReRAM	15:30-17:00 Area 12: F-9: Spintronics (IV) - Device and Circuits -	15:30-16:30 Area 11: G-9: Nanomaterial Applications	15:30-16:25 Area 2: H-9: Image Sensor	15:30-16:45 Area 14: I-9: Crystalline and Thin Film Silicon Solar Cell ( II )			

### Area Scope

Area 1: Advanced Si Processing & Materials Science  
 Area 2: Advanced Interconnect /3-D Integration Science  
 Area 3: CMOS Devices / Device Physics  
 Area 4: Advanced Memory Technology  
 Area 5: Advanced Circuits and Systems

Area 6: Compound Semiconductor Electron Devices and Related Technologies  
 Area 7: Photonic Devices and Optoelectronic Integration  
 Area 8: Advanced Material Synthesis and Crystal Growth Technology  
 Area 9: Physics and Application of Novel Functional Devices and Materials  
 Area 10: Organic Materials Science, Device Physics, and Applications

Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)  
 Area 12: Spintronic Materials and Devices  
 Area 13: Application of Nanotubes, Nanowires, and Graphene  
 Area 14: Photovoltaics & Power Semiconductor Devices